

ABSTRACT

An optical semiconductor device comprises a semiconductor laser (11) including a lower clad layer, an  
5 active layer (4), and an upper layer formed in this order,  
an electroabsorptive modulator (12) including the lower  
clad, a light absorption layer (6), and the upper clad  
layer formed in this order, and a separation region (13)  
provided between the semiconductor laser and the  
10 electroabsorptive modulator. The upper clad layer extends  
from the semiconductor laser through the separation region  
to the electroabsorptive modulator and up to the side of  
the separation region.